

Application Data Sheet

Application Information

Application Type:: Regular
Subject Matter:: Utility
Suggested Group Art Unit:: N/A
CD-ROM or CD-R?:: None
Sequence submission?:: None
Computer Readable Form (CRF)?:: No
Title:: MULTILEVEL SEMICONDUCTOR
MEMORY, WRITE/READ METHOD
THERETO/THEREFROM AND STORAGE
MEDIUM STORING WRITE/READ
PROGRAM
Attorney Docket Number:: 21737-00013-US2
Request for Early Publication?:: No
Request for Non-Publication?:: No
Total Drawing Sheets:: 10
Small Entity?:: No
Petition included?:: No
Secrecy Order in Parent Appl.?:: No

Applicant Information

Applicant Authority Type:: Inventor
Primary Citizenship Country:: Japan
Status:: Full Capacity
Given Name:: Katsuki
Family Name:: Hazama
City of Residence:: Tokyo-to
Country of Residence:: Japan
Street of mailing address:: c/o Nippon Steel Corporation
6-3, Otemachi 2-chome

City of mailing address:: Chiyoda-ku, Tokyo-to
State or Province of mailing address::
Country of mailing address:: Japan

Correspondence Information

Correspondence Customer Number:: 30678

Representative Information

Representative Customer Number:: 30678

Domestic Priority Information

Application::	Continuity Type::	Parent Application::	Parent Filing Date::
This Application	Divisional of	09/438,295	11/12/1999
This Application	Divisional of	08/931,519	09/16/1997

Foreign Priority Information

Country::	Application number::	Filing Date::	Priority Claimed::
Japan	267844	09/18/96	Yes
Japan	342663	12/06/96	Yes

Assignee Information

Assignee name:: Nippon Steel Corporation
6-3, Otemachi 2-chome
Chiyoda-ku, Tokyo-to, JAPAN